TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

## TC74LVX4051FT,TC74LVX4052FT,TC74LVX4053FT

TC74LVX4051FT 8-Channel Analog Multiplexer/Demultiplexer TC74LVX4052FT Dual 4-Channel Analog Multiplexer/Demultiplexer TC74LVX4053FT Triple 2-Channel Analog Multiplexer/Demultiplexer

The TC74LVX4051/4052/4053FT are high-speed, low-voltage drive analog multiplexer/demultiplexers using silicon gate CMOS technology. In 3 V and 5 V systems these can achieve high-speed operation with the low power dissipation that is a feature of CMOS.

The TC74LVX4051/4052/4053FT offer analog/digital signal selection as well as mixed signals. The 4051 has an 8-channel configuration, the 4052 has an 4-channel × 2 configuration, and the 4053 has a 2-channel × 3 configuration.

The switches for each channel are turned ON by the control pin digital signals.

Although the control signal logical amplitude ( $V_{CC}$  – GND) is small, the device can perform large-amplitude ( $V_{CC}$  –  $V_{EE}$ ) signal switching.

For example, if  $V_{CC} = 3 V$ , GND = 0 V, and  $V_{EE} = -3 V$ , signals between -3 V and +3 V can be switched from the logical circuit using a single 3 V power supply.

All input pins are equipped with a newly developed input protection circuit that avoids the need for a diode on the plus side (forward side from the input to the VCC). As a result, for example, 5 V signals can be permitted on the inputs even when the power supply voltage to the circuits is off. As a result of this input power protection, the TC74LVX4051/4052/4053FT can be used in a variety of applications, including in the system which has two power supplies, and in battery backup circuits.

### Features

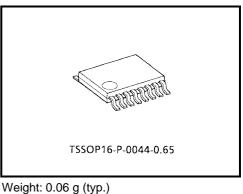
• Low ON resistance:  $R_{on} = 22 \Omega$  (typ.) (V<sub>CC</sub> - V<sub>EE</sub> = 3 V)

 $R_{on} = 15 \ \Omega \ (typ.) \ (V_{CC} - V_{EE} = 6 \ V)$ 

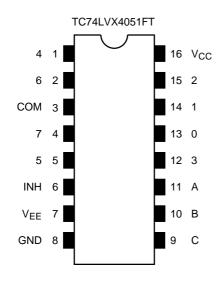
- High speed:  $t_{pd} = 3 \text{ ns} (typ.) (V_{CC} = 3.0 \text{ V})$
- Low power dissipation:  $I_{CC} = 4 \ \mu A \ (max) \ (Ta = 25^{\circ}C)$
- Input level:  $V_{IL} = 0.8 V (max) (V_{CC} = 3 V)$

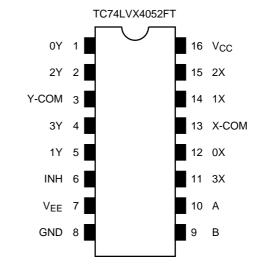
$$V_{IH} = 2.0 V (min) (V_{CC} = 3 V)$$

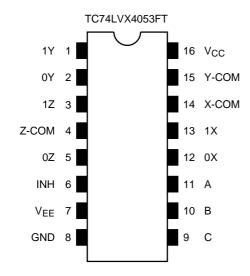
- Power down protection is provided on all control inputs
- Pin and function compatible with 74HC4051/4052/4053



### Pin Assignment (top view)







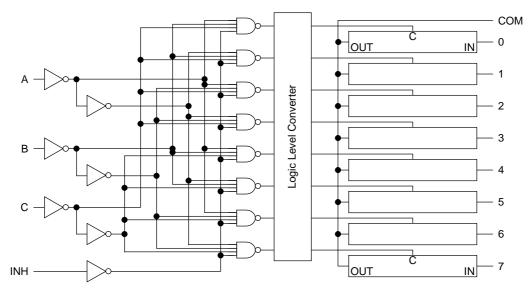
## **Truth Table**

	Contro	l Inputs		"ON" Channel				
Inhibit	C*	В	А	LVX4051FT	LVX4052FT	LVX4053FT		
L	L	L	L	0	0X, 0Y	0X, 0Y, 0Z		
L	L	L	Н	1	1X, 1Y	1X, 0Y, 0Z		
L	L	Н	L	2	2X, 2Y	0X, 1Y, 0Z		
L	L	н	н	3	3X, 3Y	1X, 1Y, 0Z		
L	н	L	L	4	—	0X, 0Y, 1Z		
L	н	L	н	5	—	1X, 0Y, 1Z		
L	Н	н	L	6	—	0X, 1Y, 1Z		
L	Н	н	н	7	—	1X, 1Y, 1Z		
Н	Х	Х	Х	None	None	None		

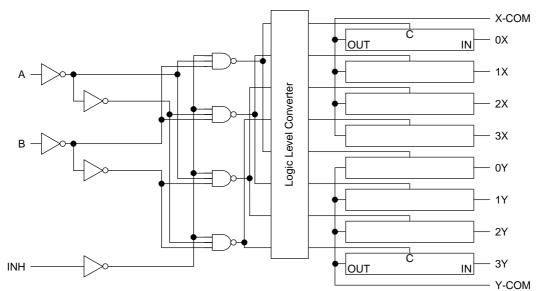
X: Don't care, \*: Except LVX4052FT

### System Diagram

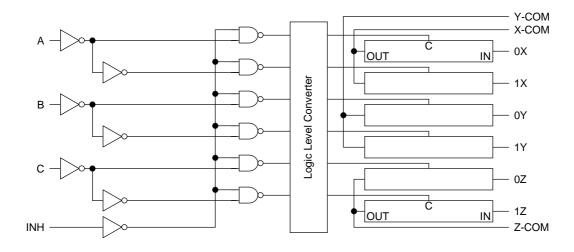
#### TC74LVX4051FT



#### TC74LVX4052FT



#### TC74LVX4053FT



## **Absolute Maximum Ratings**

Characteristics	Symbol	Rating	Unit
Power supply voltage	V <sub>CC</sub>	-0.5~7.0	V
i owei supply voltage	$V_{CC} \sim V_{EE}$	-0.5~7.0	v
Control input voltage	V <sub>IN</sub>	-0.5~7.0	V
Switch I/O voltage	V <sub>I/O</sub>	$V_{EE} - 0.5  V_{CC} + 0.5$	V
Input diode current	I <sub>IK</sub>	-20	mA
I/O diode current	I <sub>IOK</sub>	±20	mA
Switch through current	Ι <sub>Τ</sub>	±25	mA
DC V <sub>CC</sub> or ground current	ICC	±50	mA
Power dissipation	PD	180	mW
Storage temperature	T <sub>stg</sub>	-65~150	°C

## **Recommended Operating Conditions**

Characteristics	Symbol	Rating	Unit	
	V <sub>CC</sub>	2~6		
Power supply voltage	V <sub>EE</sub>	-4~0	V	
	$V_{CC} \sim V_{EE}$	2~6		
Input voltage	V <sub>IN</sub>	0~6.0	V	
Switch I/O voltage	V <sub>I/O</sub>	V <sub>EE</sub> ~V <sub>CC</sub>	V	
Operating temperature	T <sub>opr</sub>	-40~85	°C	
Input rise and fall time	dt/dv	0~100 (V_{CC} = 3.3 $\pm$ 0.3 V)	ns/V	
	ui/uv	0~20 (V <sub>CC</sub> = 5 $\pm$ 0.5 V)	ns/v	

### **Electrical Characteristics**

### **DC Electrical Characteristics**

Characteristics		Symbol Test Condition				Ta = 25°C			Ta = -40~85°C		Unit
Characte	Characteriolice		Test Condition	$V_{EE}$ (V)	$V_{CC}(V)$	Min	Тур.	Max	Min	Max	Unit
					2.0	1.5			1.5		
	High-level	VIH			3.0	2.0	_	_	2.0	_	
	i ligii-level	۷IH	_		4.5	3.15	_	_	3.15	_	
Input voltage					6.0	4.2			4.2		V
mput voltage					2.0			0.5	_	0.5	v
	Low-level	VIL			3.0			0.8	—	0.8	
	LOW ICVCI	۹Ľ			4.5			1.35	—	1.35	
					6.0			1.8	_	1.8	
				GND	2.0		200		_		
		R <sub>ON</sub>	$V_{IN} = V_{IL} \text{ or } V_{IH}$ $V_{I/O} = V_{CC} \text{ to } V_{EE}$ $I_{I/O} = 2 \text{ mA}$	GND	3.0		45	86	—	108	Ω
				GND	4.5		24	37	—	46	
ON resistance				-3.0	3.0		17	26	_	33	
			V <sub>IN</sub> = V <sub>IL</sub> or V <sub>IH</sub> V <sub>I/O</sub> = V <sub>CC</sub> or V <sub>EE</sub>	GND	2.0		28	73	—	84	
				GND	3.0		22	38	_	44	
			$I_{I/O} = 2 \text{ mA}$	GND	4.5		17	27	—	31	
				-3.0	3.0		15	24	—	28	
			$V_{IN} = V_{IL} \text{ or } V_{IH}$ $V_{I/O} = V_{CC} \text{ to } V_{EE}$	GND	2.0		10	25	—	35	Ω
Difference of O resistance betw		$\Delta R_{ON}$		GND	3.0		5	15	_	20	
switches	leen	ANON	$I_{I/O} = 2 \text{ mA}$	GND	4.5		5	13	_	18	52
			1/0 - 2 11/4	-3.0	3.0		5	10	_	15	
Input/Output lea	akage	V <sub>OS</sub> = V <sub>CC</sub> or GNE		GND	3.0			±0.25	_	±2.5	
current (switch OFF)		I <sub>OFF</sub>	F $V_{IS} = GND$ to $V_{CC}$ $V_{IN} = V_{IL}$ or $V_{IH}$	-3.0	3.0		_	±0.5	_	±5.0	μΑ
Input/Output lea	akage	lini	$V_{OS} = V_{CC}$ or GND $V_{IN} = V_{IL}$ or $V_{IH}$	GND	3.0			±0.25	_	±2.5	μA
current (switch ON, out	put open)			-3.0	3.0	_		±0.5	_	±5.0	
Control input cu	urrent	I <sub>IN</sub>	$V_{IN} = V_{CC}$ or GND	GND	6.0	_		±0.1		±0.1	μA
<b>O</b> ution of the	h			GND	3.0			4.0		40.0	
Quiescent supp	by current	ICC	$V_{IN} = V_{CC}$ or GND	-3.0	3.0		—	8.0		80.0	μA

## AC Electrical Characteristics (C<sub>L</sub> = 50 pF, Input: $t_r = t_f = 3 \text{ ns}$ , GND = 0 V)

Characteristics	Symbol	Та	st Condition			-	Га = 25°С	2	Ta = -40~85°C		Unit
Characteristics	Symbol	Test Condition		$V_{EE}(V)$	$V_{CC}(V)$	Min	Тур.	Max	Min	Max	Unit
		All types		GND	2.0	_	3.2	6.0		6.9	ns
Phase difference between	φI/O			GND	3.0	_	1.8	3.0		3.5	
input and output	ψι/Ο	Ап туре	55	GND	4.5	_	1.3	1.8	_	2.1	115
				-3.0	3.0		1.1	1.3	_	1.5	
				GND	2.0		9.0	17	_	20	
Output enable time	t <sub>pZL</sub>	Figure	1 (Note 1)	GND	3.0	_	5.7	9.0	_	11	ns
	t <sub>pZH</sub>	rigule		GND	4.5		4.5	6.0	_	7.0	115
				-3.0	3.0		5.8	8.0	_	10	
				GND	2.0		13.5	21		25	ns
Output disable time	t <sub>pLZ</sub>	Figure	1 (Note 1)	GND	3.0		11.3	15		18	
	t <sub>pHZ</sub>	rigule i		GND	4.5	_	10.3	12	_	14	
				-3.0	3.0	_	10.9	13	_	15	
Control input capacitance	C <sub>in</sub>	All type	es (Note 2)	_	_	_	5	10	_	10	pF
		4051	Figure 2 (Note 2)		3.0	_	11	25	5	25	pF
COMMON terminal capacitance	C <sub>IS</sub>	4052		-3.0			9	20	—	20	
		4053					7	15		3.5 2.1 1.5 20 11 7.0 10 25 18 14 15 10 25	
		4051	Figure 2				6	13		13	
SWITCH terminal capacitance	C <sub>OS</sub>	4052	Figure 2 (Note 2)	-3.0	3.0	_	6	13		13	pF
		4053					6	13		13	
		4051					3	6		6	
Feedthrough capacitance	C <sub>IOS</sub>	4052	Figure 2 (Note 2)	-3.0	3.0	—	3	6		6	pF
		4053	· · · /				3	6		6	
		4051	Figure 2 (Note 3)			_	14				
Power dissipation capacitance	C <sub>PD</sub>	4052		GND	6.0		24	$ $ _	—	—	pF
		4053	, , , , , , , , , , , , , , , , , , ,				18				

Note1:  $R_L = 1 k\Omega$ 

Note2:  $C_{in}$ ,  $C_{IS}$ ,  $C_{OS}$  and  $C_{IOS}$  are guaranteed by the design.

Note3: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance of IC which is calculated from the operating current consumption without load.

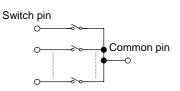
Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$ 

## \*Analog Switch Characteristics (GND = 0 V, Ta = 25°C)

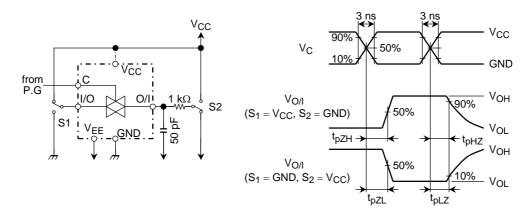
Characteristics	Symbol	Test Condition			Tun	Unit	
Characteristics	Symbol	Test Condition		V <sub>EE</sub> (V)	V <sub>CC</sub> (V)	тур.	Offic
			$V_{IN} = 2.0 V_{p-p}$	0	3.0	0.100	
Sine Wave Distortion (T.H.D)		$R_L = 10 \text{ k}\Omega, C_L = 50 \text{ pF},$ $f_{IN} = 1 \text{ kHz}$	$V_{IN} = 4.0 V_{p-p}$	0	4.5	0.030 %	%
			$V_{IN} = 6.0 V_{p-p}$	-0.3	3.0	0.020	
			4051			150	MHz
			4052	0	3.0	180	
		Adjust f <sub>IN</sub> voltage to obtain 0dBm at V <sub>OS</sub> .	4053			200	
Frequency response		Increase f <sub>IN</sub> frequency until dB	4051			150	
(switch ON)	f <sub>max</sub>	meter reads –3dB.	4052	0	4.5	180	
(Switch Oly)		$R_L = 50 \Omega$ , $C_L = 10 pF$ , $f_{IN} = 1 MHz$ , sine wave	4053			200	
		Figure 3	4051			150	
			4052	-3.0	3.0	180	
			4053			200	
		$V_{IN}$ is centered at $(V_{CC} - V_{EE})/2$ .	0	3.0	-45		
		Adjust input for 0dBm.	0	4.5	_15		
		$R_L = 600 \ \Omega$ , $C_L = 50 \ pF$ , $f_{IN} = 1 \ M$	-		-40		
Feed through attenuation (switch OFF)		Figure 4	-3.0	3.0	-45	dB	
				0	3.0	-60	
		$R_L$ = 50 $\Omega,C_L$ = 10 pF, $f_{IN}$ = 1 MHz, sine wave		0	4.5	-60	
				-3.0	3.0	-60	
Crosstalk		$R_L = 600 \ \Omega, \ C_L = 50 \ pF, \ f_{IN} = 1 \ M$	Hz, square wave	0	3.0	90	
(control input to signal		$(t_r = t_f = 6 \text{ ns})$		0	4.5	150	mV
output)		Figure 5		-3.0	3.0	0.030 0.020 150 180 200 150 180 200 150 180 200 -45 -45 -45 -45 -60 -60 90	
Crosstalk		Adjust $V_{IN}$ to obtain 0dBm at input	0	3.0	-45		
(between any switches)		$R_{L}$ = 600 $\Omega$ , $C_{L}$ = 50 pF, $f_{IN}$ = 1 M	0	4.5	-45	dB	
		Figure 6		-3.0	3.0	-45	

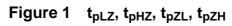
\*: These characteristics are determined by design of devices.



# AC Test Circuit

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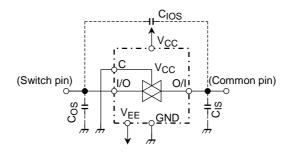
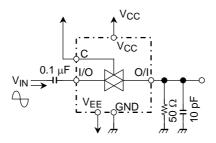


Figure 2 C<sub>IOS</sub>, C<sub>IS</sub>, C<sub>OS</sub>





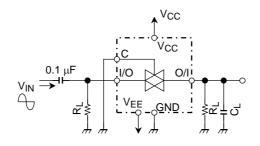
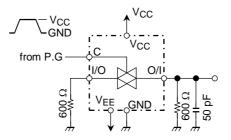
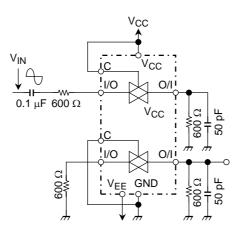
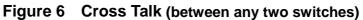


Figure 4 Feedthrough



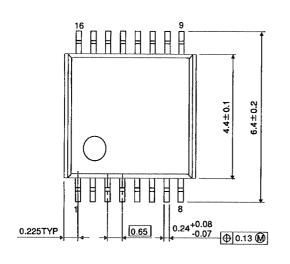


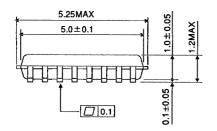


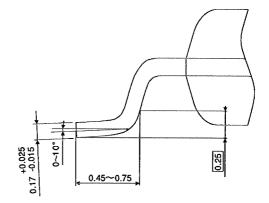


### **Package Dimensions**

#### TSSOP16-P-0044-0.65







Weight: 0.06 g (typ.)

Unit : mm

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